## **MAXIMUM RATINGS**

MAXIMOM RATINGS					
Rating	Symbol	2N3634 2N3635	2N3636 2N3637	Unit	
Collector-Emitter Voltage	VCEO	- 140	- 175	Vdc	
Collector-Base Voltage	VCBO	- 140	- 175	Vdc	
Emitter-Base Voltage	VEBO	-5.0		Vdc	
Collector Current — Continuous	lc	-1.0		Adc	
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	1.0 5.71		Watt mW/°C	
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	5.0 28.6		Watts mW/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C	

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175	°C/W
Thermal Resistance, Junction to Case	$R_{\theta}$ JC	35	°C/W

## 2N3634 thru 2N3637

CASE 79-04, STYLE 1 TO-39 (TO-205AD)





# GENERAL PURPOSE TRANSISTORS

PNP SILICON

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$  unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = 0)	2N3634, 2N3635 2N3636, 2N3637	V(BR)CEO	140 175	_	Vdc
Collector-Base Breakdown Voltage ( $I_C = -100 \mu Adc, I_E = 0$ )	2N3634, 2N3635 2N3636, 2N3637	V(BR)CBO	- 140 175		Vdc
Emitter-Base Breakdown Voltage $I_E = -10 \mu Adc, I_C = 0$		V <sub>(BR)EBO</sub>	5.0	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -100 Vdc, I <sub>E</sub> = 0)		ICBO	_	- 100	nAdc
Emitter Cutoff Current (VEB = -3.0 Vdc, I <sub>C</sub> = 0)		IEBO	_	50	nAdc
ON CHARACTERISTICS					
DC Current Gain ( $I_C = -0.1 \text{ mAdc}$ , $V_{CE} = -10 \text{ Vdc}$ )	2N3634, 2N3636 2N3635, 2N3637	hFE	40 80	_	<del></del>
$(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})$	2N3634, 2N3636 2N3635, 2N3637		45 90	_	
$(I_{C} = -10 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})(1)$	2N3634, 2N3636 2N3635, 2N3637		50 100	_	
$(I_{C} = -50 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})(1)$	2N3634, 2N3636 2N3635, 2N3637		50 100	150 300	
$(I_{C} = -150 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})(1)$	2N3634, 2N3636 2N3635, 2N3637		25 50	<u>-</u>	
Collector-Emitter Saturation Voltage(1) $(I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc})$ $(I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$		V <sub>CE(sat)</sub>		-0.3 -0.5	Vdc
Base-Emitter Saturation Voltage(1) $(I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc})$ $(I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$		V <sub>BE(sat)</sub>	 -0.65	- 0.8 - 0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product $(V_{CE} = -30 \text{ Vdc}, I_{C} = -30 \text{ mAdc}, f = 100 \text{ MHz})$	2N3634, 2N3636 2N3635, 2N3637	fŢ	150 200	_	MHz

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Motorola Small-Signal Transistors, FETs and Diodes Device Data

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**ELECTRICAL CHARACTERISTICS** (continued) (T<sub>A</sub> = 25°C unless otherwise noted.)

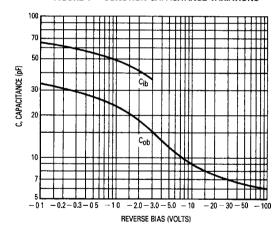
Characteristic		Symbol	Min	Max	Unit
Output Capacitance (V <sub>CB</sub> = -20 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	_	10	рF
Input Capacitance ( $V_{EB} = -1.0 \text{ Vdc}$ , $I_{C} = 0$ , $f = 1.0 \text{ MHz}$ )		C <sub>ibo</sub>	_	75	pF
	3634, 2N3636 3635, 2N3637	h <sub>ie</sub>	100 200	600 1200	ohms
Voltage Feedback Ratio (I <sub>C</sub> = $-10$ mAdc, V <sub>CE</sub> = $-10$ Vdc, f = 1.0 kHz)		h <sub>re</sub>	_	3.0	X 10-4
-	3634, 2N3636 3635, 2N3637	h <sub>fe</sub>	40 80	160 320	_
Output Admittance $\{I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc, } f = 1.0 \text{ kHz}\}$		h <sub>oe</sub>	_	200	μmhos
Noise Figure (I <sub>C</sub> = $-0.5$ mAdc, V <sub>CE</sub> = $-10$ Vdc, R <sub>S</sub> = 1.0 k ohms, f = 1.0 kHz	)	NF		3.0	dB

## SWITCHING CHARACTERISTICS

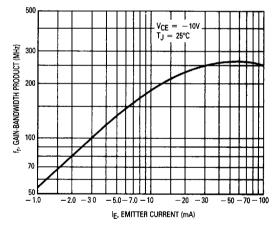
Turn-On Time	$V_{CC} = -100 \text{ Vdc}, V_{BE} = 4.0 \text{ Vdc},$	ton	_	400	ns
Turn-Off Time	$I_{C} = -50 \text{ mAdc}, I_{B1} = I_{B2} = -5.0 \text{ mAdc}$	toff	_	600	ns

<sup>(1)</sup> Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

### FIGURE 1 — JUNCTION CAPACITANCE VARIATIONS



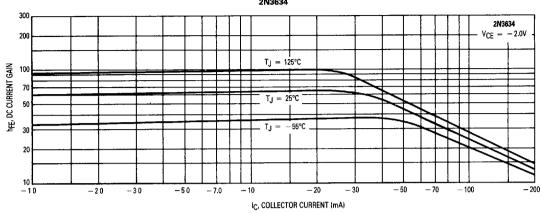
### FIGURE 2 — GAIN-BANDWIDTH PRODUCT



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FIGURE 3 — CURRENT GAIN CHARACTERISTICS versus JUNCTION TEMPERATURE 2N3634



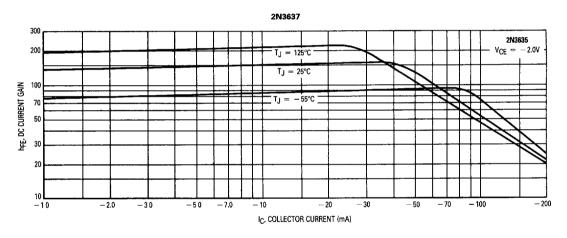
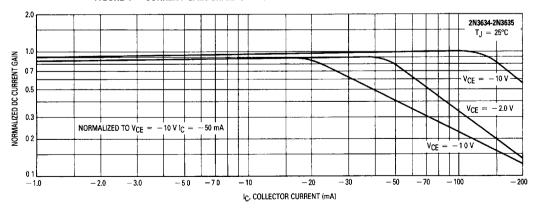


FIGURE 4 — CURRENT GAIN CHARACTERISTICS versus COLLECTOR EMITTER VOLTAGE

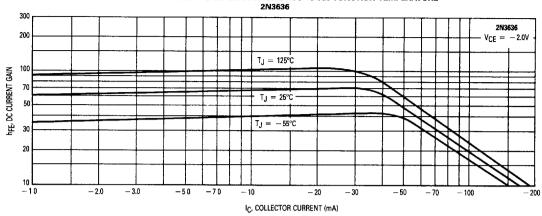


Motorolo Small Signal Transistors, FETs and Diodes Device Data

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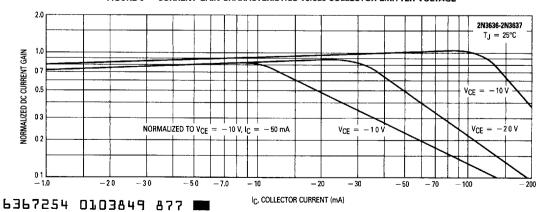
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#### 2N3637 300 Tj = 125°C 2N3637 200 $V_{CE} = -2.0V$ T<sub>J</sub> = 25°C 100 hFE, DC CURRENT GAIN $T_J = -55^{\circ}C$ 70 50 30 20 10 - 2.0 -5.0 -10 -30-70-30IC, COLLECTOR CURRENT (mA)

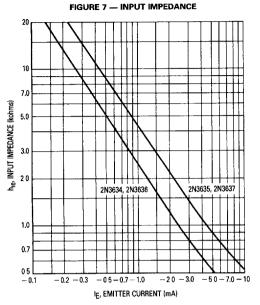
## FIGURE 6 — CURRENT GAIN CHARACTERISTICS versus COLLECTOR EMITTER VOLTAGE

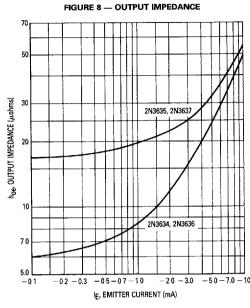


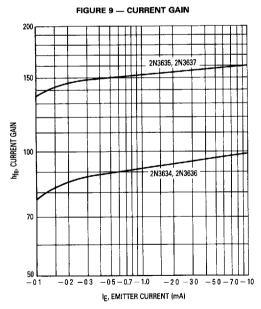
Motorola Small-Signal Transistors, FETs and Diodes Device Data

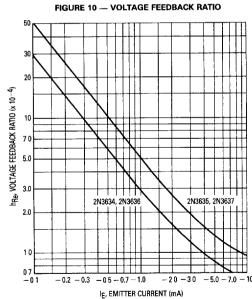
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### 2N3634 thru 2N3637



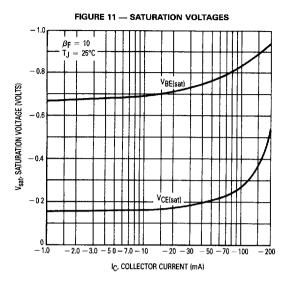






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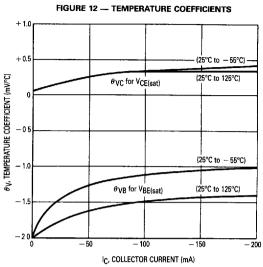
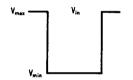
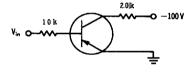
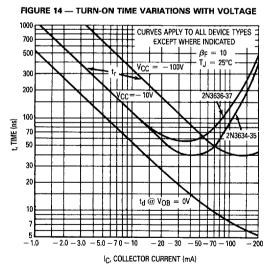


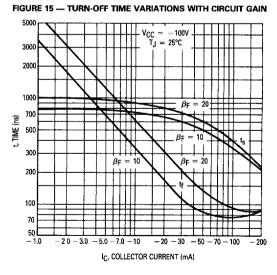
FIGURE 13 - SWITCHING TIME TEST CIRCUIT



P.W. $\simeq$ 20 $\mu$ s Duty cycle $\leq$ 2% Rise time $\leq$ 20 ns				
	V <sub>max</sub>	V <sub>min</sub>		
TURN-ON TURN-OFF	+4.0 V +4.1 V	−5.65 V −5.9 V		







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Motorola Small-Signal Transistors, FETs and Diodes Device Data

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